NHUMB11/1/2 series

80 V, 100 mA PNP/PNP resistor-equipped double transistors
Rev. 1 — 23 July 2020 Product data sheet

1. General description

PNP/PNP Resistor-Equipped double Transistor (RET) family in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	R1	R2		Package	NPN/NPN	NPN/PNP
	kΩ	kΩ	Nexperia	JEITA	complement:	complement:
NHUMB11	10	10	SOT363	SC-88	NHUMH11	NHUMD3
NHUMB1	22	22			NHUMH1	NHUMD2
NHUMB2	47	47			NHUMH2	NHUMD12

2. Features and benefits

- 100 mA output current capability
- High breakdown voltage
- · Built-in resistors
- · Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- · Digital applications
- Cost saving alternative for BC856 series in digital applications
- Controlling IC inputs
- Switching loads

4. Quick reference data

Table 2. Quick reference data

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Per transis	Per transistor						
V_{CEO}	collector-emitter voltage	open base	-	-	-80	V	
Io	output current		-	-	-100	mA	



5. Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1	□6 □5 □4	O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2		R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
3	O1	output (collector) TR1	-	
				GND1 I1 O2 aaa-019790

6. Ordering information

Table 4. Ordering information

Type number	Package						
	Name	Description	Version				
NHUMB11	SC-88	plastic surface-mounted package; 6 leads	SOT363				
NHUMB1							
NHUMB2							

7. Marking

Table 5. Marking

Type number	Marking code [1]				
NHUMB11	2B%				
NHUMB1	6C%				
NHUMB2	6E%				

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V _{CBO}	collector-base voltage	open emitter		-	-80	V
V _{CEO}	collector-emitter voltage	open base		-	-80	V
V _{EBO}	emitter-base voltage	open collector		-	-10	V
V _I	input voltage	1				
	NHUMB11			-40	+10	V
	NHUMB1			-60	+10	V
	NHUMB2			-80	+10	V
Io	output current			-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	235	mW
Per device		1				
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	350	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.

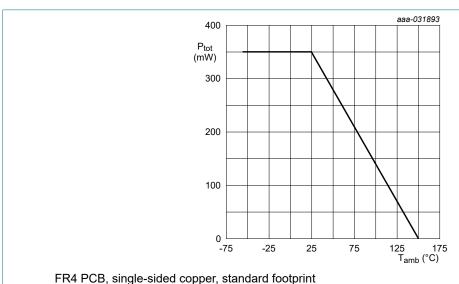


Fig. 1. Per device: Power derating curve SOT363 (SC-88)

9. Thermal characteristics

Table 7. Thermal characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor								
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	532	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	150	K/W	
Per device								
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	358	K/W	

[1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.

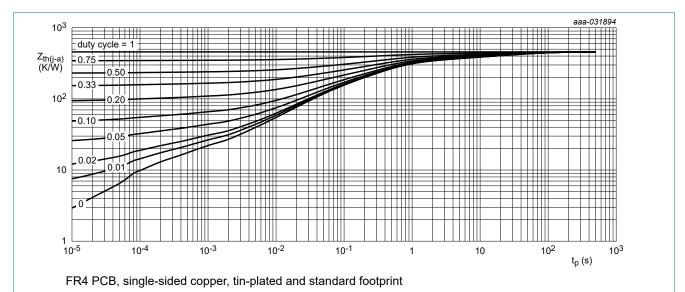


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

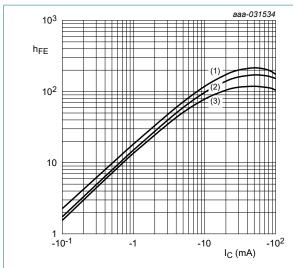
Table 8. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transis	tor				1		1		
V _{(BR)CBO}	collector-base breakdown voltage	I _C = -100 μA; I _E = 0 A		-80	-	-	V		
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = -2 mA; I _B = 0 A		-80	-	-	V		
I _{CBO}	collector-base cut-off current	$V_{CB} = -80 \text{ V}; I_E = 0 \text{ A}$		-	-	-100	nA		
I _{CEO}	collector-emitter cut-off	V _{CE} = -60 V; I _B = 0 A		-	-	-100	nA		
	current	V _{CE} = -60 V; I _B = 0 A; T _j = 150 °C		-	-	-5	μA		
I _{EBO}	emitter-base cut-off curr	ent			'				
	NHUMB11	V _{EB} = -7 V; I _C = 0 A		-	-	-600	μA		
	NHUMB1	-				-270	μΑ		
	NHUMB2			-	-	-130	μΑ		
h _{FE}	DC current gain								
	NHUMB11	V _{CE} = -5 V; I _C = -10 mA			-	-			
	NHUMB1				-	-			
	NHUMB2			100	-	-			
V _{CEsat}	collector-emitter saturation voltage	I _C = -10 mA; I _B = -0.5 mA		-	-	-100	mV		
V _{I(off)}	off-state input voltage	V _{CE} = -5 V ; I _C = -100 μA		-	-1.15	-0.8	V		
V _{I(on)}	on-state input voltage								
	NHUMB11	V _{CE} = -0.3 V ; I _C = -10 mA		-2.5	-1.8	-	V		
	NHUMB1			-3	-2.3	-	V		
	NHUMB2	-		-5	-3.3	-	V		
R1	bias resistor 1 (input)		[1]		'				
	NHUMB11			7	10	13	kΩ		
	NHUMB1			15.4	22	28.6	kΩ		
	NHUMB2			33	47	61	kΩ		
R2/R1	bias resistor ratio		[1]	8.0	1	1.2			
f _T	transition frequency	V _{CE} = -5 V; I _C = -10 mA; f = 100 MHz	[2]	-	150	-	MHz		
C _c	collector capacitance	V _{CB} = -10 V; I _E = i _e = 0 A; f = 1 MHz		-	-	3	pF		

^[1] See section "Test information" for resistor calculation and test conditions

^[2] Characteristics of built-in transistor

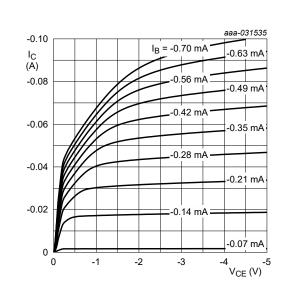


$$V_{CE} = -5 V$$

(2)
$$T_{amb}$$
 = 25 °C

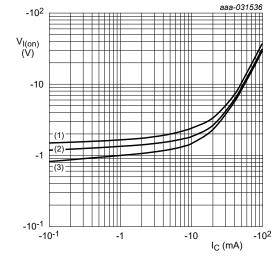
(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 3. NHUMB11: DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 4. NHUMB11: Collector current as a function of collector-emitter voltage; typical values

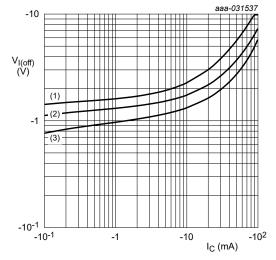


$$V_{CE}$$
 = -0.3 V

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(3)
$$T_{amb}$$
 = 100 °C

Fig. 5. NHUMB11: On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. NHUMB11: Off-state input voltage as a function of collector current; typical values

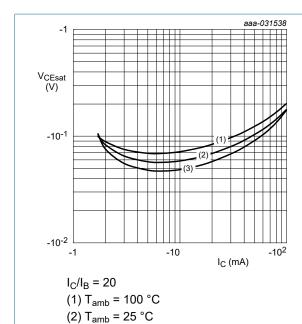
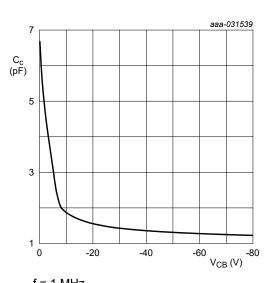


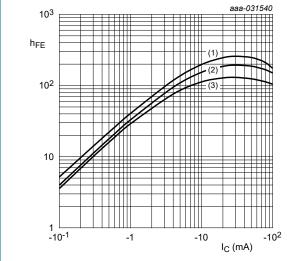
Fig. 7. NHUMB11: Collector-emitter saturation voltage as a function of collector current; typical values

(3) $T_{amb} = -40 \, ^{\circ}C$



f = 1 MHz $T_{amb} = 25 °C$

Fig. 8. NHUMB11: Collector capacitance as a function of collector-base voltage; typical values



 $V_{CE} = -5 V$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 9. NHUMB1: DC current gain as a function of collector current; typical values

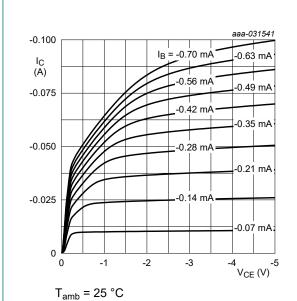
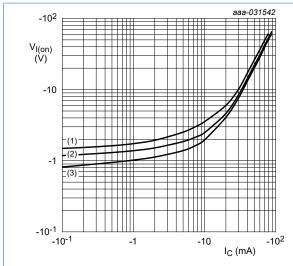


Fig. 10. NHUMB1: Collector current as a function of collector-emitter voltage; typical values



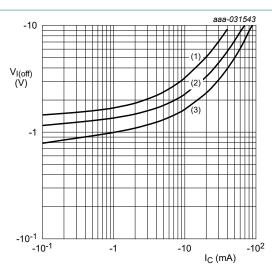
$$V_{CE}$$
 = -0.3 V

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb}$$
 = 100 °C

Fig. 11. NHUMB1: On-state input voltage as a function of collector current; typical values



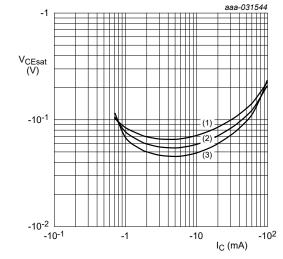
$$V_{CE} = -5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 12. NHUMB1: Off-state input voltage as a function of collector current; typical values



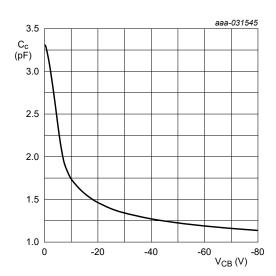
$$I_{\rm C}/I_{\rm B} = 20$$

$$(1) T_{amb} = 100 °C$$

(2)
$$T_{amb}$$
 = 25 °C

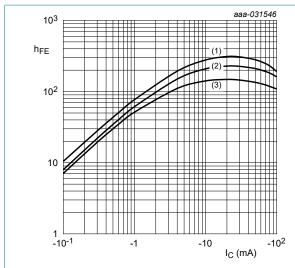
(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 13. NHUMB1: Collector-emitter saturation voltage as a function of collector current; typical values



$$f = 1 MHz$$

Fig. 14. NHUMB1: Collector capacitance as a function of collector-base voltage; typical values

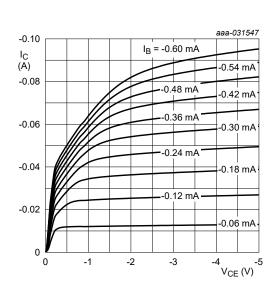


$$V_{CE} = -5 V$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

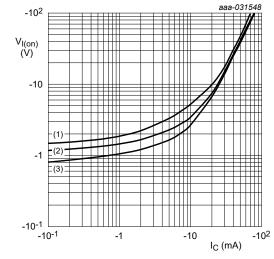
(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 15. NHUMB2: DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 16. NHUMB2: Collector current as a function of collector-emitter voltage; typical values

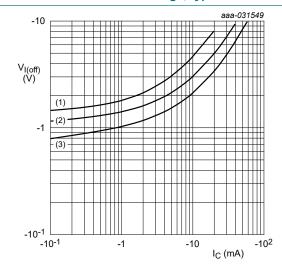


$$V_{CE}$$
 = -0.3 V

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 17. NHUMB2: On-state input voltage as a function of collector current; typical values

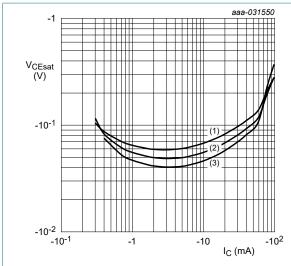


$$V_{CE} = -5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 18. NHUMB2: Off-state input voltage as a function of collector current; typical values



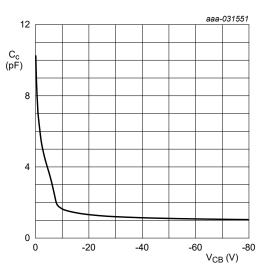
$$I_C/I_B = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

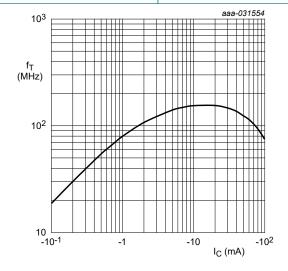
Fig. 19. NHUMB2: Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz

$$T_{amb}$$
 = 25 °C

Fig. 20. NHUMB2: Collector capacitance as a function of collector-base voltage; typical values of built-in transistor



f = 100 MHz

 $V_{CE} = -5 V$

T_{amb} = 25 °C

Fig. 21. Transition frequency as a function of collector current; typical values of built-in transistor

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

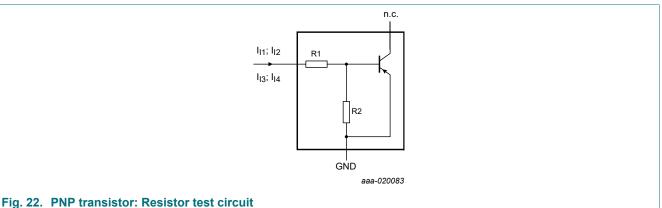
Resistor calculation

Calculation of bias resistor 1 (R1)

$$R_I = \frac{V(I_{I2}) - V(I_{II})}{I_{I2} - I_{II}}$$

Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

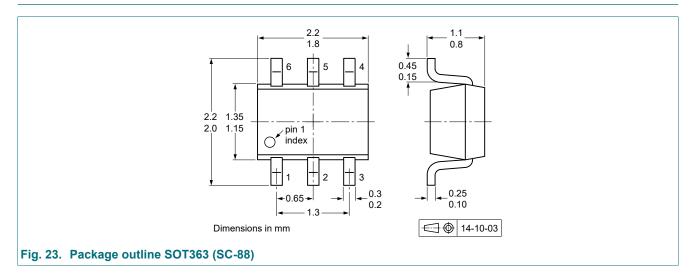


Resistor test conditions

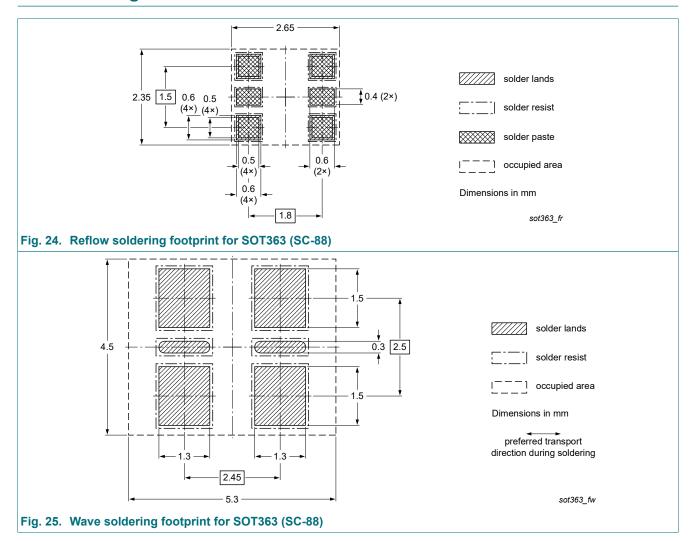
Table 9. Resistor test conditions

Type number	R1 (kΩ)	R2 (kΩ)	Test conditi	Test conditions				
			I _{I1}	I _{I2}	I _{I3}	I ₁₄		
Per transistor								
NHUMB11	10	10	-800 µA	-1.1 mA	350 μΑ	450 μΑ		
NHUMB1	22	22	-550 μA	-750 μA	150 µA	230 μΑ		
NHUMB2	47	47	-250 μA	-350 µA	55 μΑ	105 µA		

12. Package outline



13. Soldering



14. Revision history

Table 10. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NHUMB11_1_2_SER v.1	20200723	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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NHUMB11_1_2_SER

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